

## Features

- Optimized Body Diode Reverse Recovery Performance
- Low On-resistance and Low Conduction Losses
- Ultra Low Gate Charge Cause Lower Driving Requirement
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## Maximum Ratings

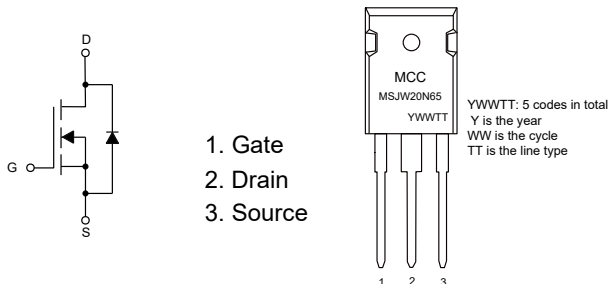
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 0.83°C/W Junction to Case

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	650	V	
Gate-Source Voltage	$V_{GS}$	±30	V	
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	20	A
		$T_C=100^\circ\text{C}$	12	A
Pulsed Drain Current (Note 1)	$I_{DM}$	60	A	
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	484	mJ	
Repetitive Avalanche Energy	$E_{AR}$	0.7	mJ	
Avalanche Current	$I_{AR}$	3.5	A	
Total Power Dissipation	$P_D$	151	W	

Note:

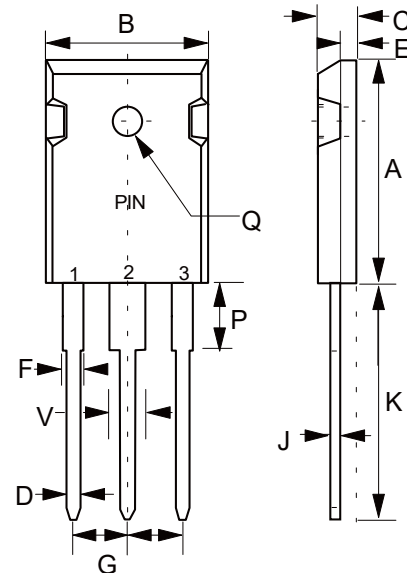
- 1.Repetitive Rating; Pulse Width Limited by Maximum Junction Temperature.
2. $I_{AS}=3.5\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$ .

## Internal Structure and Marking Code



# N-CHANNEL Super-Junction Power MOSFET

## TO-247



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.787	0.866	20.00	22.00	
B	0.598	0.638	15.20	16.20	
C	0.185	0.208	4.70	5.30	
D	0.035	0.059	0.90	1.50	
E	0.059	0.094	1.50	2.40	
F	0.067	0.091	1.70	2.30	
J	0.019	0.031	0.48	0.80	
K	0.748	0.833	19.00	21.15	
P	0.122	0.189	3.10	4.80	
Q	0.118	0.150	3.00	3.80	Φ
V	0.106	0.134	2.70	3.40	
G	0.197	0.224	5.00	5.70	

**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	650			V	
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 30V$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V, T_C=25^\circ C$			1	$\mu A$	
		$V_{DS}=650V, V_{GS}=0V, T_C=125^\circ C$			100		
Gate-Threshold Voltage <sup>(Note 3)</sup>	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5		4.5	V	
Drain-Source On-Resistance <sup>(Note 3)</sup>	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A$		150	170	m $\Omega$	
Gate Resistance <sup>(Note 3)</sup>	$R_G$	f = 1.0MHz Open Drain		12		$\Omega$	
<b>Dynamic Characteristics <sup>(Note 4)</sup></b>							
Input Capacitance	$C_{iss}$	$V_{DS}=100V, V_{GS}=0V, f=1MHz$		1724		$\mu F$	
Output Capacitance	$C_{oss}$			61			
Reverse Transfer Capacitance	$C_{rss}$			6			
Total Gate Charge	$Q_g$	$V_{DS}=520V, V_{GS}=10V, I_D=20A$		39		nC	
Gate-Source Charge	$Q_{gs}$			8			
Gate-Drain Charge	$Q_{gd}$			15			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=400V, I_D=20A$ $V_{GS}=10V, R_{GEN}=25\Omega$		15		ns	
Turn-On Rise Time	$t_r$			59			
Turn-Off Delay Time	$t_{d(off)}$			121			
Turn-Off Fall Time	$t_f$			44			
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=20A$			1.2	V	
Continuous Body Diode Current	$I_S$				20	A	
Reverse Recovery Time	$t_{rr}$	$V_R=400V, I_F=I_S,$ $di_F/dt = 100A/\mu s$		423		ns	
Reverse Recovery Charge	$Q_{rr}$				5.3		$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$				25		A

Note:

3.Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$  .

4.Guaranteed by Design, not Subject to Production.

## Curve Characteristics

Fig. 1 - Typical Output Characteristics

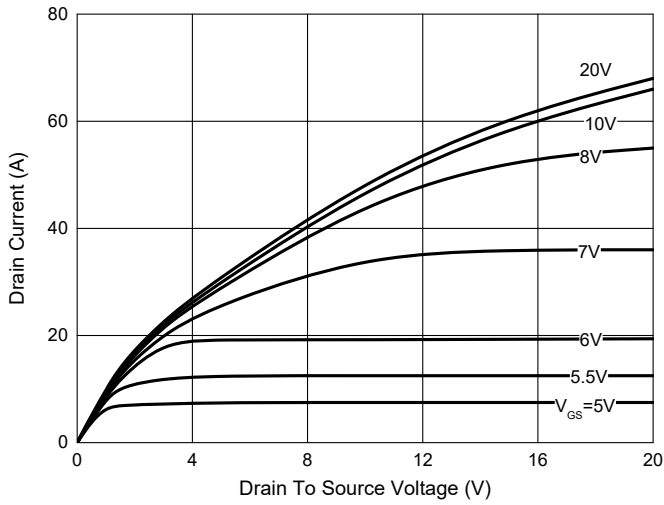


Fig. 2 - Transfer Characteristics

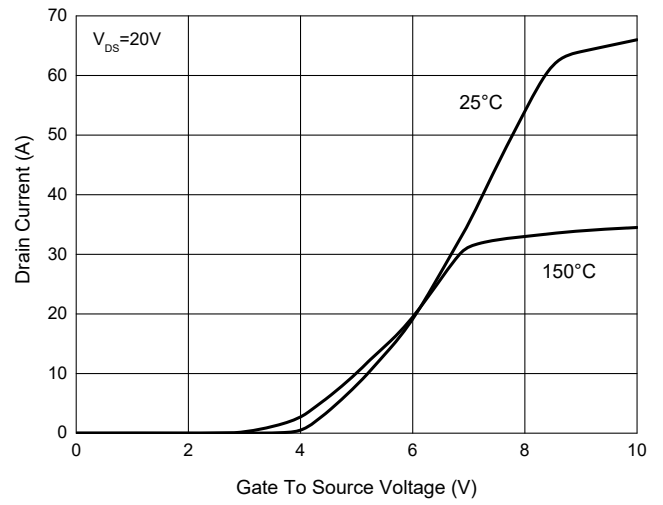


Fig. 3 -  $R_{DS(ON)} - I_D$

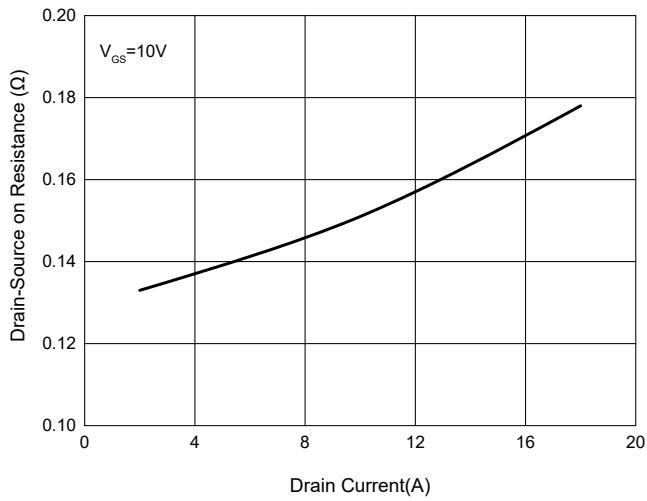


Fig. 4 - Capacitance Characteristics

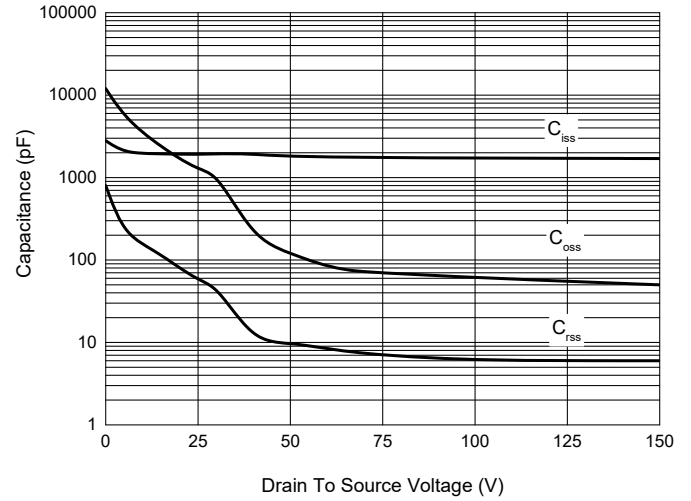


Fig. 5 - Total Gate Charge Characteristics

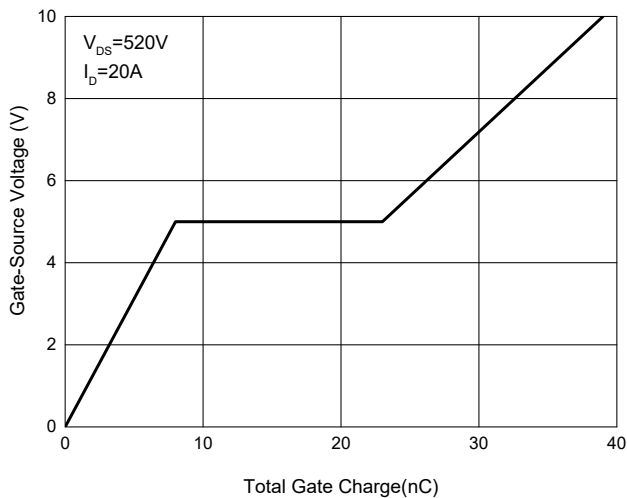
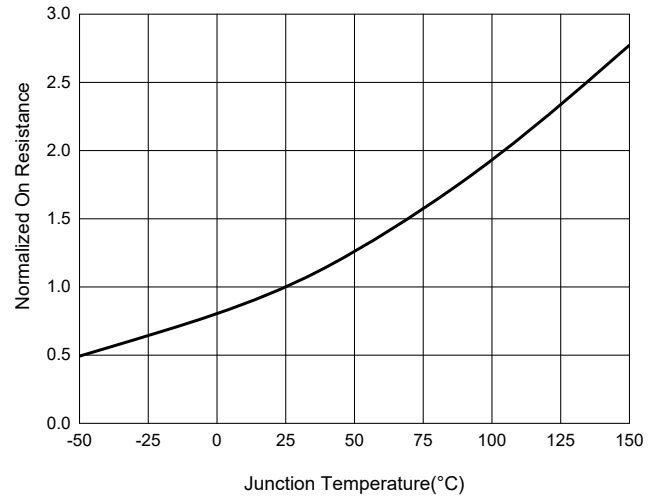


Fig. 6 - Normalized On Resistance Characteristics



## Ordering Information

Device	Packing
MSJW20N65-BP	Tube:30pcs/Tube, 360pcs/Box,1.8K/Ctn;

Note : Adding "-HF" Suffix For Halogen Free, eg. Part Number-BP-HF

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